## MT2301

### MT2301 Single P-Channel Power MOSFET

MOS-TECH Semiconductor Co.,LTD 臺 灣 茂 鈿 半 導 體 股 份 有 限 公 司

#### **General Description**

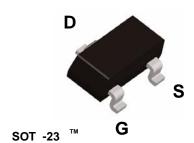
This P-Channel Power MOSFET is produced MOS-TECH Semiconductor's using advanced PowerTrench process that has been especially tailored to minimize the on-state r esistance and yet maintain low gate charge for superior switching performance.

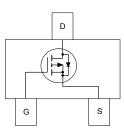
These devices a re well suited for portable electronics applications: load s witching and power management, battery charging circuits and DC/DC conversion.



#### Features

- -3.3 A, -20 V.  $R_{DS(ON)}$  = 0.072  $\Omega$  @ V<sub>GS</sub> = -4.5 V  $R_{DS(ON)} = 0.096\Omega @ V_{GS} = -2.5 V$
- Low gate charge (3.6 nC typical)
- High performance trench technology for extremely low R<sub>DS(ON)</sub>
- SuperSOT<sup>TM</sup> -23 provides low  $R_{DS(ON)}$  and 30% higher power handling capability than SOT23 in the same footprint





#### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V <sub>DSS</sub>	Drain-Source Voltage		-20	V	
V <sub>GSS</sub>	Gate-Source Voltage		±12	V	
I <sub>D</sub>	Drain Current – Continuous	(Note 1a)	-3.3	A	
	– Pulsed		-10		
P <sub>D</sub>	Maximum Power Dissipation	(Note 1a)	0.5	W	
		(Note 1b)	0.46		
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C	

#### **Thermal Characteristics**

R <sub>0JA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

### **Package Marking and Ordering Information**

Device Marking	Device	Reel Size	Tape width	Quantity
010X	MT2301	7"	8mm	3000 units

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Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CHAR	ACTERISTICS		•	•		
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-20			V
$\Delta BV_{DSS} / \Delta T_{J}$	Breakdown Voltage Temp. Coefficient	$I_{\rm D}$ = -250 µA, Referenced to 25 °C		-16		mV /°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -16 V, V <sub>GS</sub> = 0 V			-1	μA
		T <sub>J</sub> = 55°C			-10	μA
I <sub>GSSF</sub>	Gate - Body Leakage, Forward	$V_{GS} = 8 V, V_{DS} = 0 V$			100	nA
GSSR	Gate - Body Leakage, Reverse	$V_{GS} = -8 V, V_{DS} = 0 V$			-100	nA
ON CHARA	CTERISTICS (Note 2)	<b>i</b>	•			
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-0.8		-1.5	V
$\Delta V_{GS(th)} / \Delta T_{J}$	Gate Threshold Voltage Temp. Coefficient	$I_{\rm D}$ = -250 µA, Referenced to 25 °C		3		mV /°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = -4.5 \text{ V}, I_{D} = -1.3 \text{ A}$		0.072	0.08	Ω
		T <sub>J</sub> =125°C		0.12	0.15	
		$V_{GS} = -2.5 V, I_{D} = -1.1 A$		0.096	0.15	
l <sub>D(ON)</sub>	On-State Drain Current	$V_{GS} = -4.5 V, V_{DS} = -5 V$	-3.3			Α
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = -4.5 \text{ V}, \ \text{I}_{D} = -2 \text{ A}$		4		S
DYNAMIC C	HARACTERISTICS					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -10 V, V_{GS} = 0 V,$ f = 1.0 MHz		330		pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		80		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			35		pF
SWITCHING	CHARACTERISTICS (Note 2)					
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{DD} = -5 V, I_{D} = -0.5 A,$ $V_{GS} = -4.5 V, R_{GEN} = 6 \Omega$		7	15	ns
r	Turn - On Rise Time			12	22	ns
t <sub>D(off)</sub>	Turn - Off Delay Time			16	26	ns
t <sub>r</sub>	Turn - Off Fall Time			5	12	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = -10 V, I_{D} = -2 A,$		3.6	5	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS}^{00} = -4.5 V$		0.8		nC
Q <sub>gd</sub>	Gate-Drain Charge			0.7		nC
DRAIN-SOU	RCE DIODE CHARACTERISTICS AND MAX					
s	Maximum Continuous Drain-Source Diode Fo	ximum Continuous Drain-Source Diode Forward Current			-0.42	А
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = -0.42 A$ (Note)		-0.7	-1.2	V

Note:

1.  $R_{gas}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the s older mounting surface of the drain pins.  $R_{gas}$  is guaranteed by design while  $R_{gas}$  is determined by the user's board design.



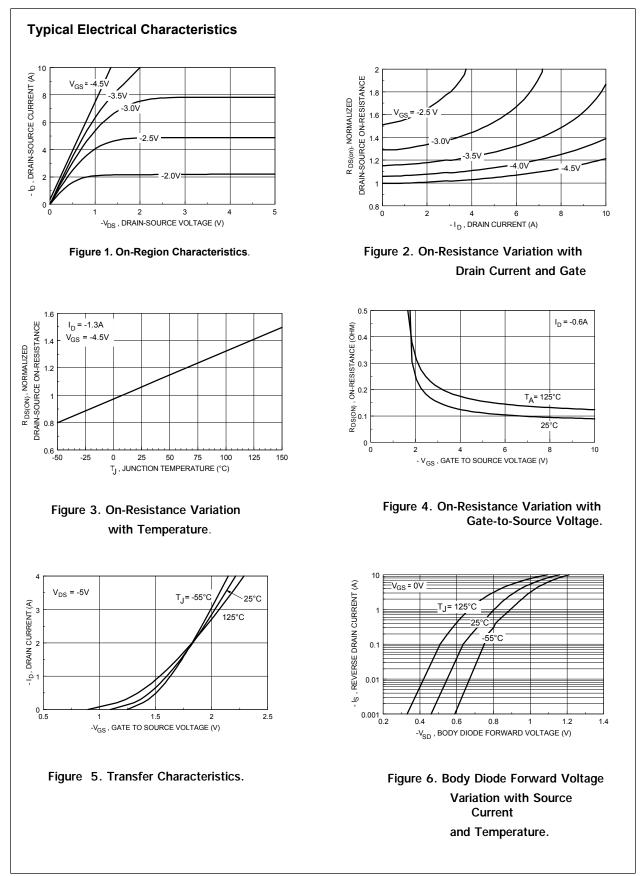
a. 250°C/W when mounted on a 0.02 in<sup>2</sup> pad of 2oz Cu.

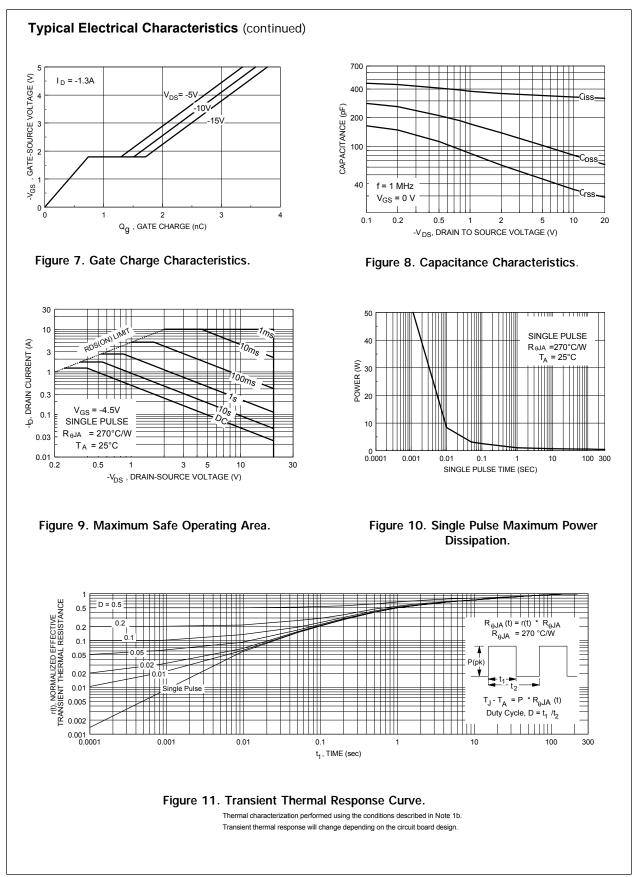


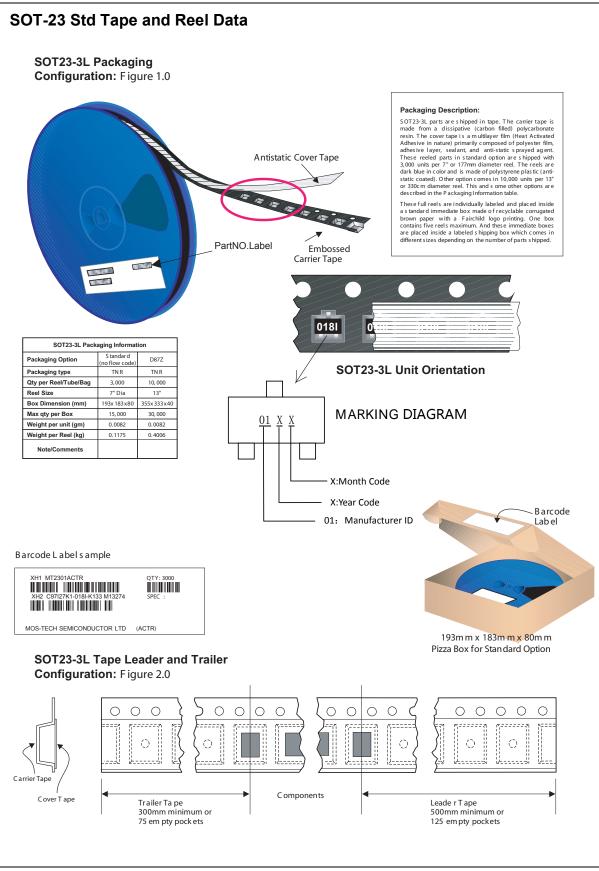
 b. 270°C/W when mounted on a 0.001 in<sup>2</sup> pad of 2oz Cu.

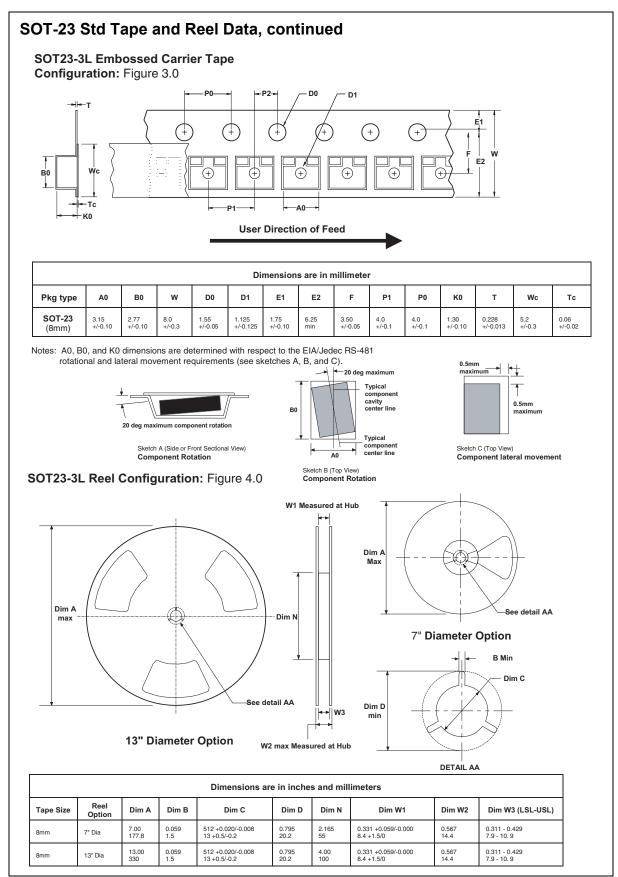
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2.0%.









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